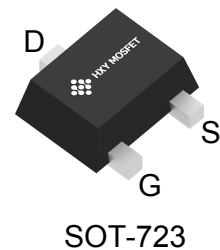




Description

The RUM002N02T2L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = 20V$ $I_D = 1.2A$

$R_{DS(ON)} < 260 m\Omega @ V_{GS}=4.5V$

$R_{DS(ON)} < 350 m\Omega @ V_{GS}=2.5V$

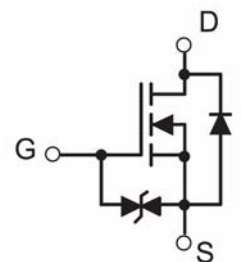
ESD Rating: 1500V HBM

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
RUM002N02T2L	SOT-723	HXY MOSFET	8000

Absolute maximum ratings ($T_a=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	1.2	A
Pulsed Drain Current	I_{DM}	1.8	A
Power Dissipation	P_D	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55~ +150	$^\circ C$



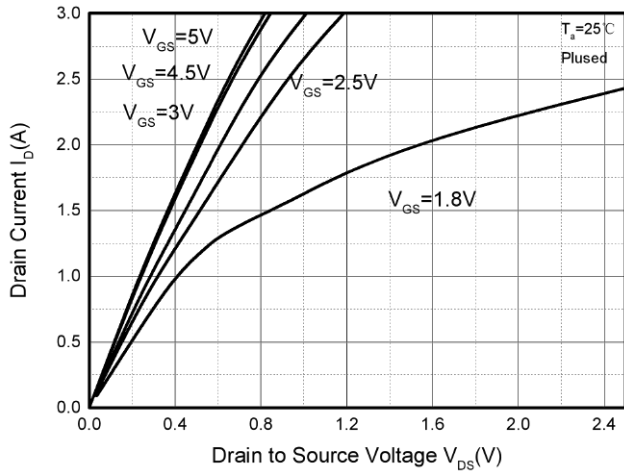
Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =16V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±10	uA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.3	0.65	1	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 1.2A		150	260	mΩ
		V _{GS} =2.5V, I _D = 0.8A		132	168	
		V _{GS} =1.8V, I _D = 0.3A		165	240	
Input Capacitance	C _{iss}	V _{DS} =16V, V _{GS} =0V, f=1MHz		79	120	pF
Output Capacitance	C _{oss}			13	20	
Reverse Transfer Capacitance	C _{rss}			9	15	
Turn-on delay time	t _{d(on)}	V _{GS} =4.5V, V _{DS} =10V, I _D =500mA, R _{GEN} =10Ω		6.7		ns
Turn-on rise time	t _r			4.8		
Turn-off delay time	t _{d(off)}			17.3		
Turn-off fall time	t _f			7.4		
Body Diode Voltage	V _{SD}	I _S =0.5A, V _{GS} = 0V		0.7	1.3	V

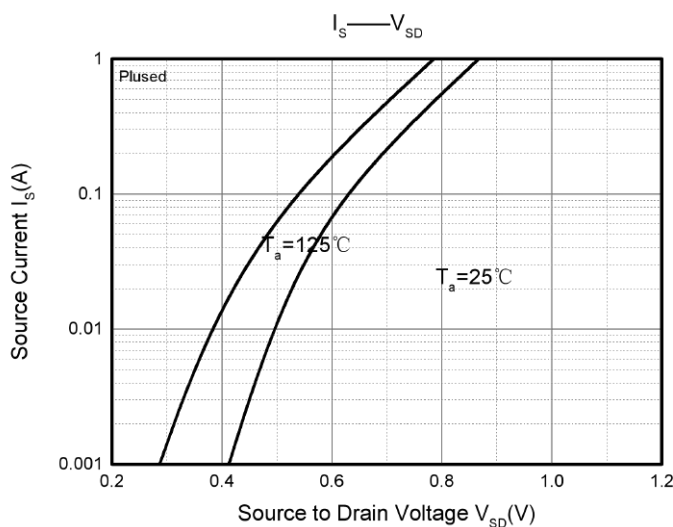
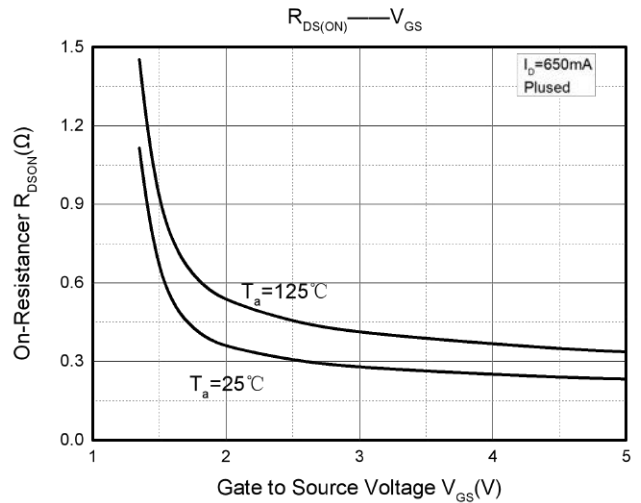
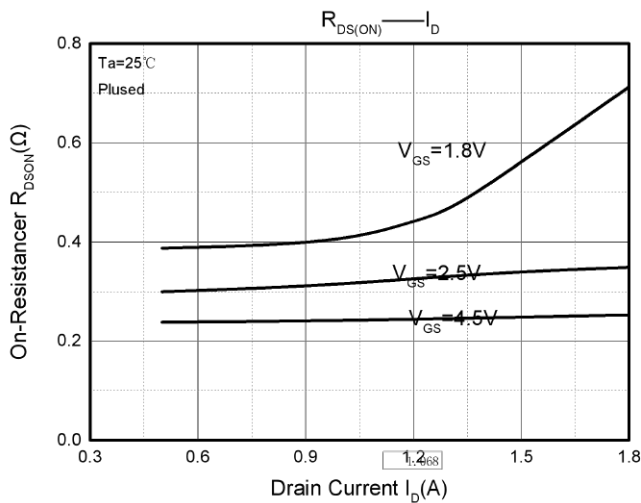
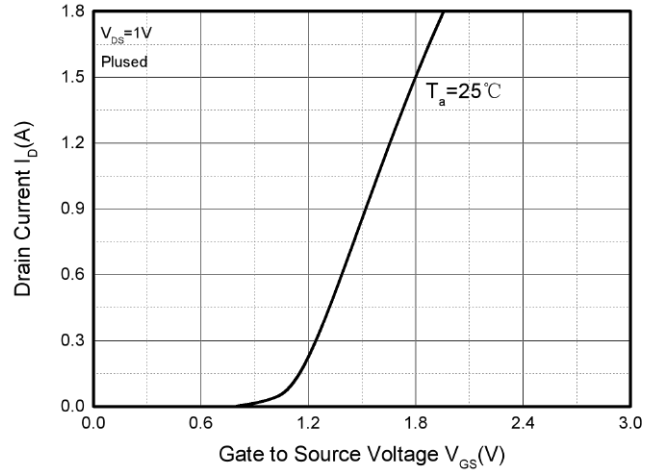


Typical Characteristics

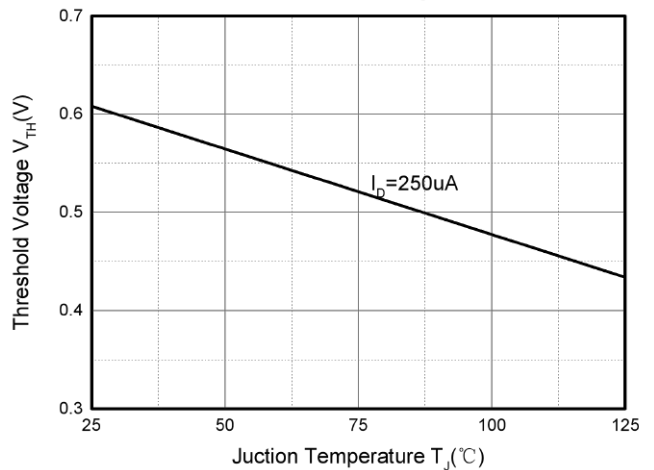
Output Characteristics



Transfer Characteristics

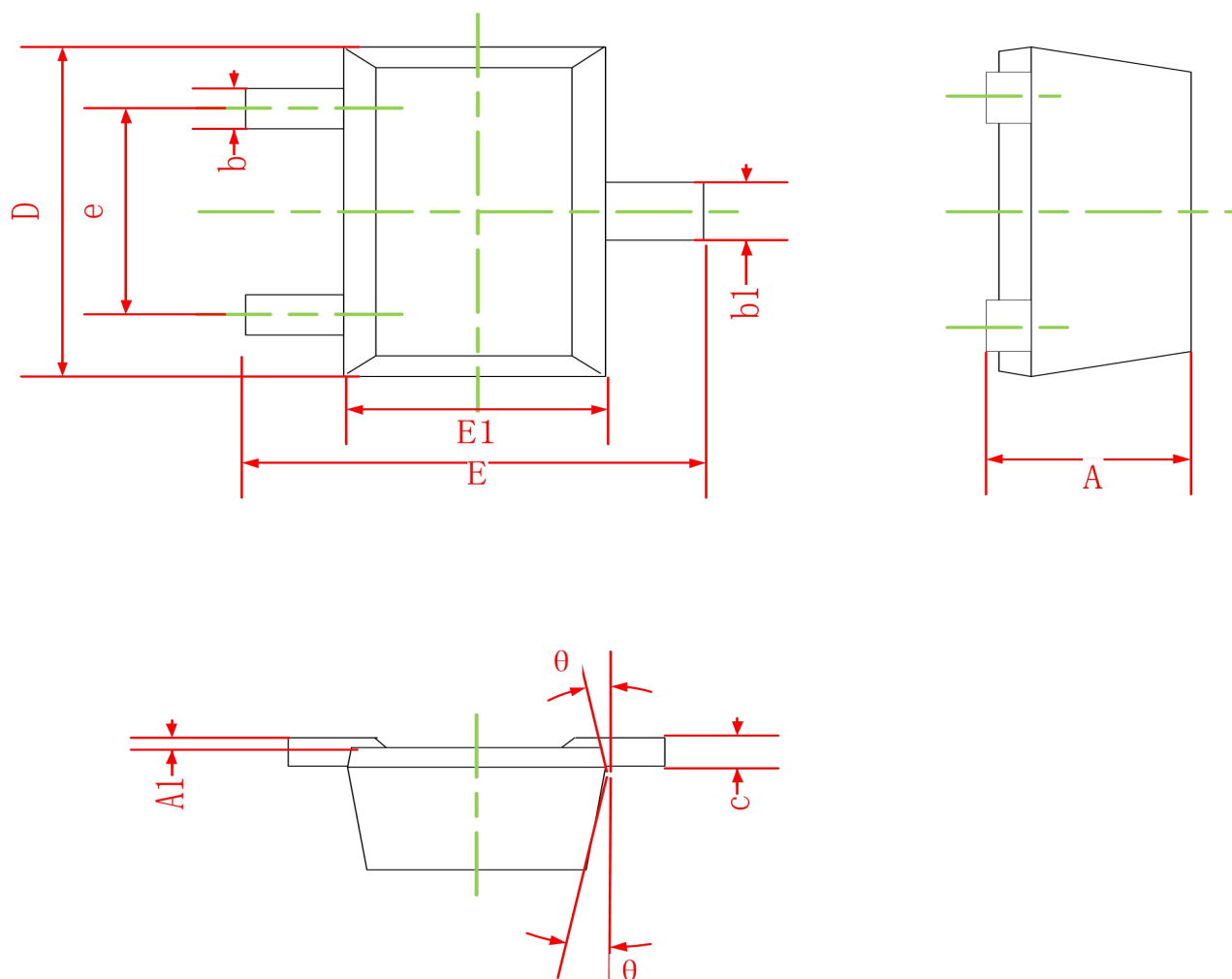


Threshold Voltage





SOT-723 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.430	0.500
A1	0.000	0.050
b	0.170	0.270
b1	0.270	0.370
c	0.080	0.150
D	1.150	1.250
E	1.150	1.250
E1	0.750	0.850
e	0.800TYP.	
θ	7° REF.	



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